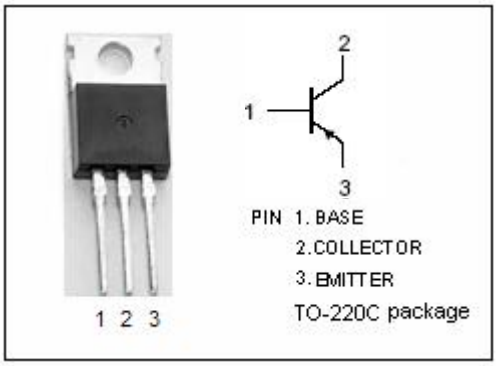
isc Silicon PNP Power Transistor — KSA940TU

DESCRIPTION

- Collector-Emitter Breakdown Voltage
  : V(BR)CEO= -150V(Min)
- DC Current Gain
  : hFE= 40-140@ IC= -0.5A
- Complement to Type KSC2073TU
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

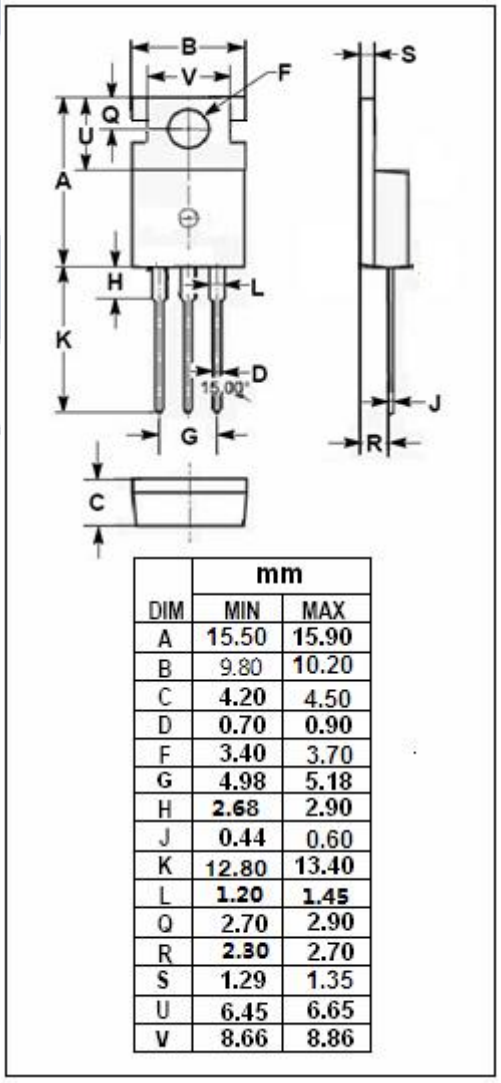
- Designed for use in general purpose power amplifier , vertical output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
P_C	Total Power Dissipation @ T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	5.0	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-150			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA ; I_E= 0	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA ; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A ; V_{CE}= -10V			-0.85	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V ; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -0.5A ; V_{CE}= -10V	40		140	
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A;V_{CE}= -10V;f_{test}= 1MHz		4		MHz